



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Young-Hee MUN

Group Art Unit: 1765

Serial No.: 09/742,127

Examiner: M. Song

Filed: December 22, 2000.

For: METHOD FOR TREATING A SEMICONDUCTOR WAFER THERMALLY
AND SEMICONDUCTOR WAFER FABRICATED BY THE SAME

TRANSMITTAL

Assistant Commissioner of Patents
Washington, D.C. 20231

Sir:

Transmitted herewith is an Amendment Under Rule 1.111 for filing in the above-captioned patent application.

The fee has been calculated as shown below:

	Claims Remaining After Amendment		Highest Number Previously Paid For	Present Extra	Small Entity Rate Addit. Fee	(or)	Other Than A Small Entity Rate Addit. Fee
Total	18	-	20 =	0	x 09 = \$		x 18 = \$
Indep.	05	-	05 =	0	x 40 = \$		x 80 = \$
___ First Presentation of Multiple Dependent Claims					+130 = \$		+ 260 = \$
Total Additional Fee					\$		\$

A check in the amount of \$_____ is attached for:

XXXX If a Petition for Extension of Time is necessary and the Petition and/or the check is not enclosed, this will act as the Petition and applicant herewith petitions the Commissioner to extend the time for response and charge any fees necessary under 37 CFR 1.17 (a)(1)-(5) to Deposit Account No. 06-1358. The Commissioner is also authorized to charge payment of any other additional fees associated with this communication or credit any overpayment to Deposit Account No. 06-1358. A duplicate copy of this sheet is attached.

Respectfully submitted,
JACOBSON HOLMAN PLLC

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Yoon S. Ham
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Atty. Docket: 12597/P66182US0
Telephone: (202)638-6666
Date: October 8, 2002
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PATENT
ATTY. DOCKET NO.: P66182US0

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AMENDMENT UNDER RULE 1.111

Assistant Commissioner
of Patents
Washington, D.C. 20231

October 8, 2002

Sir:

In response to the Office Action (Paper No. 7) dated July 9, 2002, kindly amend
the above-identified patent application as follows:

IN THE CLAIMS

Please cancel claim 6 without prejudice or disclaimer, and amend claims 1, 8 and
17-19 to read as follows:

1. (Amended) A method of treating a wafer thermally to remove defects contained in single
crystalline semiconductor, the method comprising the steps of:

carrying out a heat treatment on the wafer at a temperature equal to or higher than
1200 °C; and

carrying out a rapid thermal annealing on the wafer at a temperature equal to or
lower than 800°C for a period having a duration of two minutes or less.

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